

PS7241C-AT1, PS7241C-AT5**CURRENT LIMIT TYPE
8-PIN SOP OCMOS FET
(2-ch OCMOS FET)****DESCRIPTION**

The 7241C-AT1 and PS7241C-AT5 are solid state relays containing a GaAs LED on the light emitting side (input side), MOS FETs, Photo transistor and current control circuit on the output side. Current control circuit of OCMOS FET protects this device from thermal breakdown and output circuit.

They are suitable for analog signal control because of their low offset and high linearity.

FEATURES

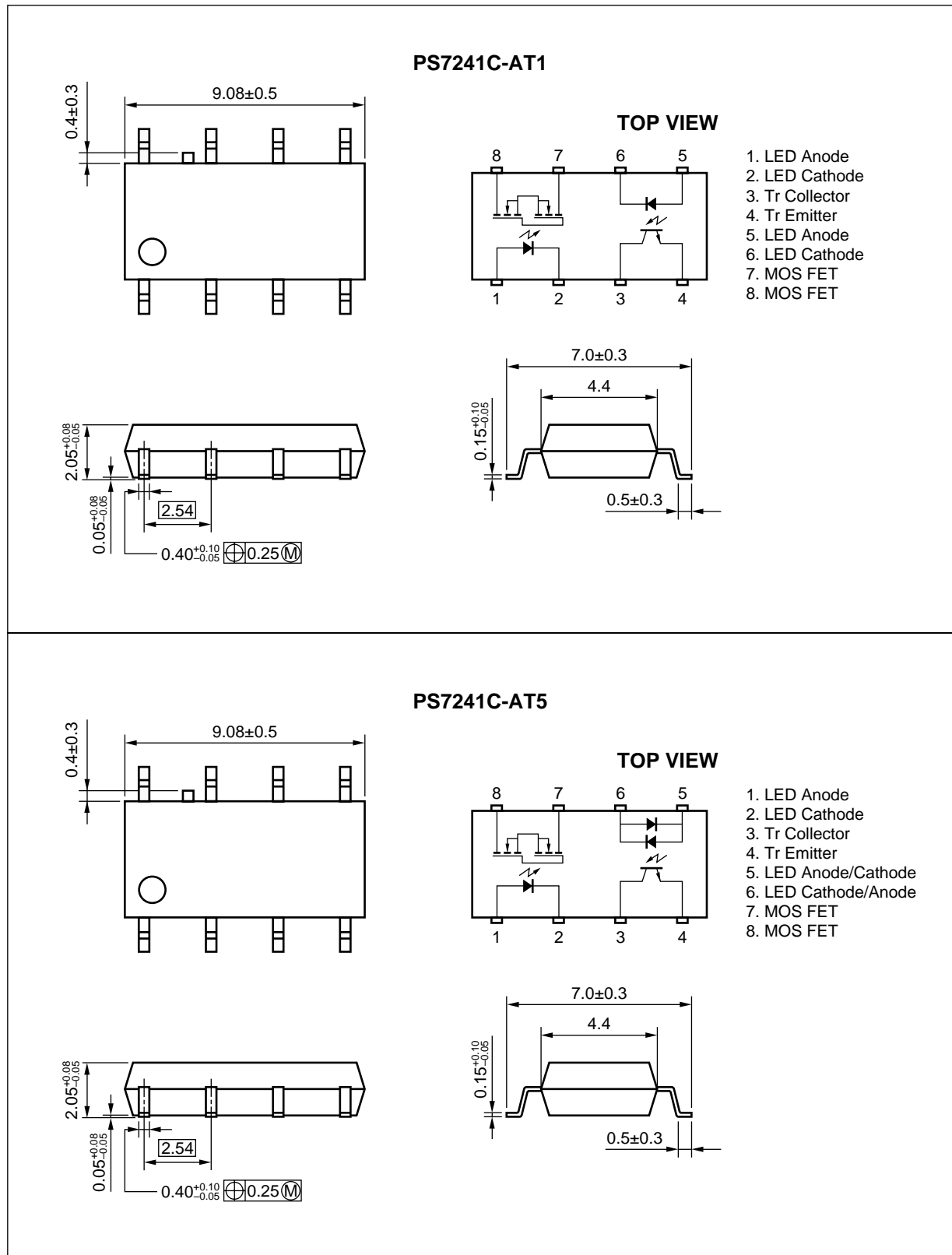
- 2 channel type (OCMOS FET + Photocoupler)
- Limit current ($I_{LMT} = 125$ to 180 mA)
- Low LED operating current ($I_F = 2$ mA)
- Designed for AC/DC switching line changer
- Small and thin package (8-pin SOP)
- Isolation voltage ($BV = 1\,500$ V_{r.m.s.})
- Low offset voltage
- Ordering number of taping product: PS7241C-AT1-F3, F4, PS7241C-AT5-F3, F4

APPLICATIONS

- Exchange equipment
- Measurement equipment
- FA/OA equipment

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

★ PACKAGE DIMENSIONS (in millimeters)



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter			Symbol	Ratings	Unit
OCMOS FET	Diode	Forward Current (DC)	I _F	50	mA
		Reverse Voltage	V _R	5.0	V
		Power Dissipation	P _D	50	mW
		Peak Forward Current ¹	I _{FP}	1	A
	MOS FET	Break Down Voltage	V _L	400	V
		Continuous Load Current	I _L	120	mA
		Power Dissipation	P _D	430	mW
Photocoupler	Diode	Forward Current	I _F	50	mA
		Reverse Voltage ²	V _R	5.0	V
		Power Dissipation	P _D	50	mW
		Peak Forward Current ¹	I _{FP}	1	A
	Transistor	Collector to Emitter Voltage	V _{CEO}	40	V
		Emitter to Collector Voltage	V _{ECO}	6	V
		Collector Current	I _C	80	mA
		Power Dissipation	P _C	100	mW
Isolation Voltage ³			BV	1 500	Vr.m.s.
Total Power Dissipation			P _T	630	mW
Operating Ambient Temperature			T _A	−40 to +80	°C
Storage Temperature			T _{stg}	−40 to +100	°C

*1 PW = 100 μs, Duty Cycle = 1 %

*2 PS7241C-AT1 only

*3 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

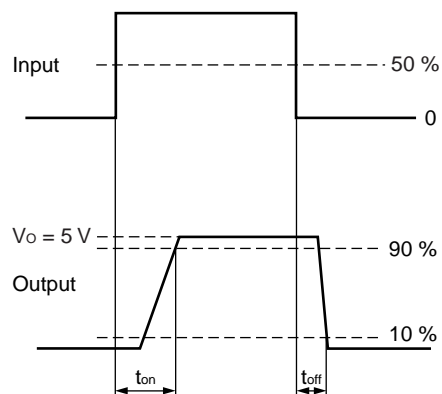
RECOMMENDED OPERATING CONDITIONS (T_A = 25 °C)

Parameter		Symbol	MIN.	TYP.	MAX.	Unit
OCMOS FET	LED Operating Current	I _F	2	20	30	mA
	LED Off Voltage	V _F	0		0.5	V
Photocoupler	LED Operating Current	I _F	2	5	20	mA

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OCMOS FET	Diode	Forward Voltage	V _F	I _F = 10 mA		1.2	1.4	V
		Reverse Current	I _R	V _R = 5 V			5.0	μA
	MOS FET	Off-state Leakage Current	I _{Loff}	V _D = 400 V		0.03	1.0	μA
		Output Capacitance	C _{out}	V = 0 V, f = 1 MHz		65		pF
	Coupled	LED On-state Current	I _{Fon}	I _L = 120 mA			2.0	mA
		On-state Resistance	R _{on1}	I _F = 10 mA, I _L = 10 mA		28	35	Ω
			R _{on2}	I _F = 10 mA, I _L = 120 mA			30	
		Turn-on Time ^{*1}	t _{on}	I _F = 10 mA, V _O = 5 V, PW ≥ 10 ms		0.5	1.0	ms
		Turn-off Time ^{*1}	t _{off}			0.08	1.0	
		Limit Current	I _{LMT}	I _F = 10 mA, V _L = 6 V, t = 5 ms	125	150	180	mA
		Isolation Resistance	R _{I-O}	V _{I-O} = 1.0 kV _{DC}	10 ⁹			Ω
		Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		0.4		pF
Photo- coupler	Diode	Forward Voltage	V _F	I _F = 10 mA		1.2	1.4	V
		Reverse Current ^{*2}	I _R	V _R = 5 V			5.0	μA
	Transistor	Collector to Emitter Dark Current	I _{CEO}	V _{CE} = 40 V, I _F = 0 mA			100	nA
		Collector to Emitter Breakdown Voltage	BV _{CEO}	I _C = 1 mA	40			V
		Emitter to Collector Breakdown Voltage	BV _{ECO}	I _E = 100 μA	6.0			
	Coupler	Current Transfer Ratio (I _C /I _F)	CTR	I _F = 5 mA, V _{CE} = 5 V	50	200	400	%
		Collector Saturation Voltage	V _{CE(sat)}	I _F = 10 mA, I _C = 2 mA			0.3	V
		Isolation Resistance	R _{I-O}	V _{I-O} = 1.0 kV _{DC}	10 ¹¹			Ω
		Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		0.4		pF
		Rise Time	t _r	V _{CC} = 5V, I _C = 2 mA, RL = 100 Ω		3.0		μs
		Fall Time	t _f			5.0		

*1 Turn-on, Turn-off time



*2 PS7241C-AT1 only

[MEMO]

[MEMO]

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CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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